Program Schedule for
International Conference on Nanostructuring with Ion Beams
(ICNIB2015)

23/11/2015, Monday

Registration 8:30 to 9:45
Opening Session 9:45 to 10:45

PL-1  J. Fassbender, HZDR, Germany  (45 minutes)
Ion induced magnetic patterning using chemical disorder induced ferromagnetism

Tea Break (10:45 to 11:15)

Session - 1 (11:15 to 12:30)

IT-1  M. Engler, HZDR, Germany
Reverse Epitaxy on Elemental Semiconductors

IT-2  A. Tripathi, IUAC, New Delhi
Swift heavy ion induced modifications in Graphene

O-1  Ranjeeta Gupta, AMITY University, Noida
Development and performance of in-situ MOKE facility to study heavy ion induced modifications in nanostructure systems

Lunch Break (12:30 to 14:00)

Session - 2 (14:00 to 16:00)

IT-3  P. Gangopadhyay, IGCAR, Kalpakkam
Synthesis of Metal Nanoparticles Using Ion-beams

IT-4  D.G. Kuberkar, SU, Rajkot
Defect Driven Modifications In Ferroelectric behavior of Multiferroic Thin Films: 200 MeV Ag^{+15} Ion Irradiation Effect

IT-5  P.K. Sahoo, NISER, Bhubaneswar
Sputtering induced nano-dot synthesis by keV ion beams of Au/Si thin films

O-2  V.V. Siva Kumar, IUAC, New Delhi
Synthesis of nanocomposite diamond/amorphous carbon films using Bias enhanced ECR CVD

O-3  Uday B. Singh, IUAC, New Delhi
Synthesis of coupled plasmonic nanostructures and its surface enhanced Raman Scattering effect

Session - 3 (16:00 to 18:00)
Poster Session with Tea

IBSI Meeting (18:15)
Dinner (19:30)
24/11/2015, Tuesday

Session- 1 (9:00 to 10:30)
PL-2 Prof. S. Seki, Kyoto, Japan
Low Dimensional Nanostructures Produced by High Energy Single Particle
IT-6 R. Singh, IIT, New Delhi
Implantation-Induced Layer Splitting of Compound Semiconductors for Advanced Substrates
O- 4 P. Mallick, North Orissa University, Baripada
Effect of film thickness on the evolution of microstructure, surface morphology and optical band gap of NiO thin films under 200 MeV Ag ion irradiation

Tea Break (10:30 to 11:00)

Session- 2 (11:00 to 12:45)
O- 5 Anuradha Verma, DEI, Agra
Photoelectrochemical Water Splitting Study on Au/ TiO₂ System modified by 500 keV Ar Ion Beam Irradiation
O- 6 Vijay Kumar, RBS College, Agra
Comparative study of modifications induced by thermal and athermal annealing in RF sputtered nanocrystalline tin oxide thin films
O- 7 Neha Bhardwaj, GGSIPU, New Delhi
Ion beam engineering of morphological, structural and optical properties of Au-SnO₂ nanocomposite thin films
O- 8 Sunil Kumar, IUAC, New Delhi
Annealing effect of swift heavy ion beam in graphene
O- 9 B. Bharati, IIT, Varanasi
Anatase to Brookite Phase Transformation in TiO₂ Thin Films Deposited by e-beam Evaporation Technique under Ar²⁺ Ion Irradiation
O-10 H.S. Lokesha, PESIT, Bangalore
Modification of structure and luminescence properties induced by swift heavy ions in ZrO₂:Sm³⁺ phosphor
O-11 Lisha Raghvan, CUSAT, Cochin
Modification of Exchange Bias in FeNiMoB-Zinc Ferrite bilayer films by Swift Heavy Ion irradiation

Lunch Break (12:45 to 14:00)

Session- 3 (14:00 to 15:00)
IT-7 P.K. Bajpai, GGU, Bilaspur
Material Science Research Using Low Energy Ion Accelerator with specific reference to National Centre for Accelerator Based Research at Bilaspur
IT-8 A. Kanjalal, SNU, Noida
Ion beam produced TiOx nanochannels for developing resistive switching memory devices

Excursion to TajMahal (15:15 to 18:30)
25-11-2015, Wednesday

Session-1 (9:00 to 10:45)

PL-3 **Prof. R. Cuerno, Madrid, Spain**
Non-uniform stress as a driving force for semiconductor surface nanostructuring by ion beams

IT-9 **K.V. Sarathlal, DESY, Germany**
Growth study of ordered magnetic nanostructures on rippled Si substrates and its applications

IT-10 **T. Deswal, Central University, Mahedragarh, Haryana**
Wetting behavior of Ripple Patterned Silicon surfaces produced by ion beam

Tea Break (10:45 to 11:15)

Session-2 (11:15 to 13:15)

IT-11 **S.V.S. Nageswarrao, CU, Hyderabad**
Ion beam characterization and modification of silicon nanoparticles and nanostructures

IT-12 **R.S. Chauhan, RBS College Agra**
SHI induced effects on thin films of metal oxides

IT-13 **P. Karaseov, St. Petersburg, Russia**
Radiation-defect induced photoluminescence in monocrystalline silicon

O-12 **S. K. Garg, IUAC, New Delhi**
Statistical analysis of ripple morphology on Si surfaces due to 60 keV Ar+-ions

O-13 **R. Nongjai, AMU, Aligarh**
Structural, morphological and magnetic properties of 200 MeV Ag^{+17} and 100 MeV O^{+7} ions irradiated CoFe_{2}O_{4} thin films

Closing